Application No.: Not Yet Assigned Docket No.: N9450,0046/P046

REMARKS

The application has been editorially revised for consistency between the specification and the drawings. Favorable action on the application is solicited.

Dated: February 22, 2002

Respectfully submitted,

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MARKED-UP VERSION SHOWING CHANGES MADE

[Fig. 4 is a diagram] Figs. 4_{10} , through 4_{10} ; are diagrams showing an example of patterns suitable for process conditions change monitoring.

[Fig. 5 is a Figs. 5; a] through 5(c) are cross-sectional [view] views showing an example of patterns suitable for process conditions change monitoring.

[Fig. 6 is a graph] Figs. 6(a) and 6(b) are graphs showing changes in edge width against focus.

[Fig. 7 is another graph] Figs. 7(a) and 7(b) are other graphs showing changes in edge width against focus.

[Fig. 9 is a diagram | Figs. 9(a) and 9(b) are diagrams showing the acquisition of the creation sequences for the models which establish logical linking between exposure conditions and dimensional characteristic quantities.

[Fig. 12 is a diagram] Figs. 12(a) and 12(b) are diagrams of the process conditions change monitoring system pertaining to the third preferred mode of embodiment.

[Fig. 13 is a diagram] Figs. 13(a) and 13(b) are diagrams showing a second example of patterns suitable for process conditions change monitoring.

[Fig. 15 is a diagram] Figs. 15(a) and 15(b) are diagrams showing a third example of patterns suitable for process conditions change monitoring.

[Fig. 16 is a diagram] Figs. 16(a) and 16(b) are diagrams showing the measuring method in the third example of patterns suitable for process conditions change monitoring.

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[Fig. 19 is an] Figs. 19 a and 19 b, are epitomic [diagram] diagrams representing the relationship between the cross-sectional shape of a resist pattern and the level of a secondary electron signal.

[Fig. 20 is a graph] Figs. 20(a) and 20(b) are graphs showing the relationship between exposure level, focus, and line width.